

ABSTRACT

A method of generating a mask for use in a photolithography process. The method includes the steps of determining a target mask pattern having a plurality of features to be imaged and an illumination system to be utilized to image the mask; identifying a critical pitch within the target pattern and optimizing illumination settings of the illumination system for imaging the critical pitch; identifying a forbidden pitch within the target pattern; and modifying the transmittance of the features having a pitch equal to or substantially equal to the forbidden pitch such that the exposure latitude of the features equal to or substantially equal to the forbidden pitch is increased.